# MOS INTEGRATED CIRCUIT $\mu PD3794$

# 2700 PIXELS $\times$ 3 COLOR CCD LINEAR IMAGE SENSOR

The  $\mu$ PD3794 is a color CCD (Charge Coupled Device) linear image sensor which changes optical images to electrical signal and has the function of color separation.

The  $\mu$ PD3794 has 3 rows of 2700 pixels, and each row has a single-sided readout type of charge transfer register. And it has reset feed-through level clamp circuits, a clamp pulse generation circuit, an RGB selector and voltage amplifiers. Therefore, it is suitable for 300 dpi/A4 color image scanners, color facsimiles and so on.

#### FEATURES

- Valid photocell  $: 2700 \text{ pixels} \times 3$
- Photocell's pitch : 8  $\mu$ m
- Line spacing : 32  $\mu$ m (4 lines) Green line-Blue line, Blue line-Red line
- Color filter : Primary colors (red, green and blue), pigment filter (with light resistance 10<sup>7</sup> lx•hour)
- Resolution : 12 dot/mm A4 (210  $\times$  297 mm) size (shorter side)
  - 300 dpi US letter (8.5"  $\times$  11") size (shorter side)
- Drive clock level : CMOS output under 5 V operation
- Data rate : 4 MHz MAX.
- Power supply : +12 V
- On-chip circuits : Reset feed-through level clamp circuits
  - Clamp pulse generation circuit RGB selector
    - Voltage amplifiers

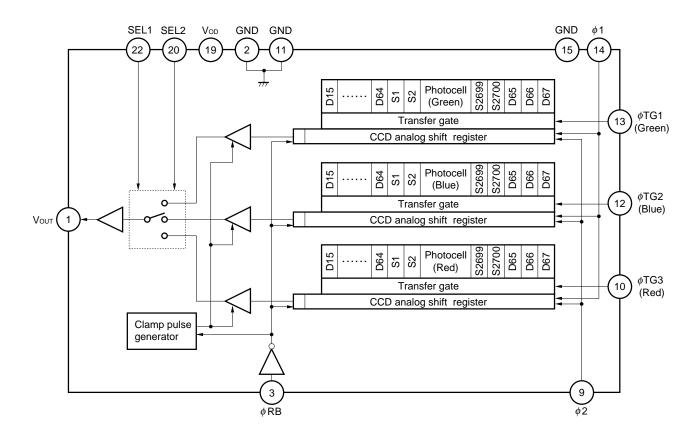
#### ORDERING INFORMATION

 Part Number
 Package

 μPD3794CY
 CCD linear image sensor 22-pin plastic DIP (400 mil)

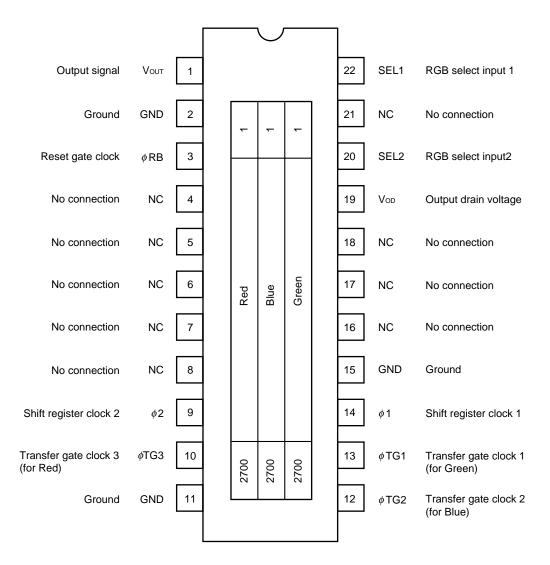
The information in this document is subject to change without notice.

#### **BLOCK DIAGRAM**

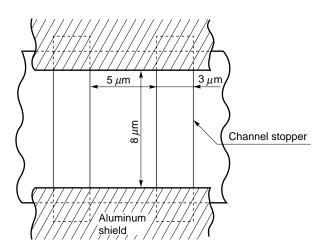


#### PIN CONFIGURATION (Top View)

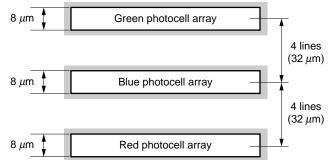
CCD linear image sensor 22-pin plastic DIP (400 mil)



#### PHOTOCELL STRUCTURE DIAGRAM



# PHOTOCELL ARRAY STRUCTURE DIAGRAM (Line spacing)



#### ABSOLUTE MAXIMUM RATINGS (TA = +25 $^{\circ}$ C)

Parameter	Symbol	Ratings	Unit
Output drain voltage	Vod	-0.3 to +15	V
Shift register clock voltage	V <sub>\$\phi1\$</sub> , V <sub>\$\phi2\$</sub>	-0.3 to +8	V
Reset gate clock voltage	V <sub>ØRB</sub>	–0.3 to +8	V
Transfer gate clock voltage	V <sub>φ</sub> τg1 to V <sub>φ</sub> τg3	-0.3 to +8	V
RGB select input voltage	VSEL1,VSEL2	–0.3 to +8	V
Operating ambient temperature	Та	-25 to +60	°C
Storage temperature	Tstg	-40 to +70	°C

# Caution Exposure to ABSOLUTE MAXIMUM RATINGS for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The parameters apply independently.

#### RECOMMENDED OPERATING CONDITIONS (TA = +25 °C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Output drain voltage	Vod	11.4	12.0	12.6	V
Shift register clock high level	V <sub>01H</sub> , V <sub>02H</sub>	4.5	5.0	5.5	V
Shift register clock low level	V <sub>01L</sub> , V <sub>02L</sub>	-0.3	0	+0.5	V
Reset gate clock high level	V <sub>Ø</sub> rbh	4.5	5.0	5.5	V
Reset gate clock low level	V <sub>Ø</sub> RBL	-0.3	0	+0.5	V
Transfer gate clock high level	Vøтg1н to Vøtg3н	4.5	$V_{\phi 1H}$ Note	V <sub>¢1H</sub> Note	V
Transfer gate clock low level	Vøtg1l to Vøtg3l	-0.3	0	+0.5	V
RGB select input high level	Vsel1h, Vsel2h	4.5	5.0	5.5	V
RGB select input low level	VSEL1L, VSEL2L	-0.3	0	+0.5	V
Data rate	f <sub>øRB</sub>	_	1.0	4.0	MHz

**Note** When Transfer gate clock high level ( $V_{\phi TG1H}$  to  $V_{\phi TG3H}$ ) is higher than Shift register clock high level ( $V_{\phi 1H}$ ), Image lag can increase.

#### ELECTRICAL CHARACTERISTICS

 $\left( \begin{array}{l} T_A = +25 \ ^{\circ}C, \ V_{OD} = 12 \ V, \ data \ rate \ (f_{\phi RB}) = 1 \ MHz, \ storage \ time = 10 \ ms, \ light \ source: \ 3200 \ K \ halogen \ lamp \ +C-500S \ (infrared \ cut \ filter, \ t = 1 \ mm), \ input \ signal \ clock = 5 \ V_{P-P} \ N_{P-P} \ N_$ 

Parameter		Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Saturation voltage	Saturation voltage			2.0	3.0		V
Saturation exposure	Red	SER			0.205		lx•s
	Green	SEG			0.225		lx•s
	Blue	SEB			0.375		lx∙s
Photo response non-unif	ormity	PRNU	Vout = 1.0 V		6	20	%
Average dark signal		ADS	Light shielding		0.5	5.0	mV
Dark signal non-uniformi	ty	DSNU	Light shielding		4.0	10.0	mV
Power consumption		Pw			300	600	mW
Output impedance		Zo			0.5	1	kΩ
Response	Red	RR		10.3	14.6	18.9	V/lx∙s
	Green	Rg		9.4	13.3	17.2	V/lx∙s
	Blue	Rв		5.6	8.0	10.4	V/lx∙s
Image lag	L	IL	Vout = 1.0 V		5.0	10.0	%
Offset level Note1	Offset level Note1			4.5	6.0	7.5	V
Output fall delay time No	te2	ta	Vout = 1.0 V		70		ns
Total transfer efficiency		TTE	Vout = 1.0 V,	92	98		%
			data rate = 4 MHz				
Response peak	Red				630		nm
	Green				540		nm
	Blue				460		nm
Dynamic range		DR1	Vsat /DSNU		750		times
		DR2	V <sub>sat</sub> /σ		3000		times
Reset feed-through noise	B Note1	RFTN	Light shielding	-1000	-300	+500	mV
Random noise		σ	Light shielding	_	1.0	_	mV

#### Notes 1. Refer to TIMING CHART 2.

**2.** When the fall time of  $\phi$ 1 (t1) is the TYP. value (refer to **TIMING CHART 2**).

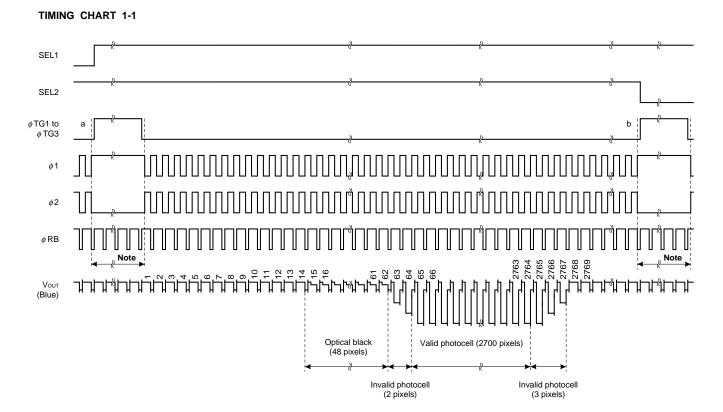
### INPUT PIN CAPACITANCE (TA = +25 °C, Vod = 12 V)

Parameter	Symbol	Pin name	Pin No.	MIN.	TYP.	MAX.	Unit
Shift register clock pin capacitance 1	C <sub>\u03c61</sub>	<i>φ</i> 1	14		300		pF
Shift register clock pin capacitance 2	C <sub>\$\phi2\$</sub>	φ2	9		300		pF
Reset gate clock pin capacitance	Cørb	φRB	3		20		pF
Transfer gate clock pin capacitance	С <sub>øтg</sub>	φTG1	13		50		pF
		φTG2	12		50		pF
		φTG3	10		50		pF
RGB select input pin capacitance	CSEL	SEL1	22		50		pF
		SEL2	20		50		pF

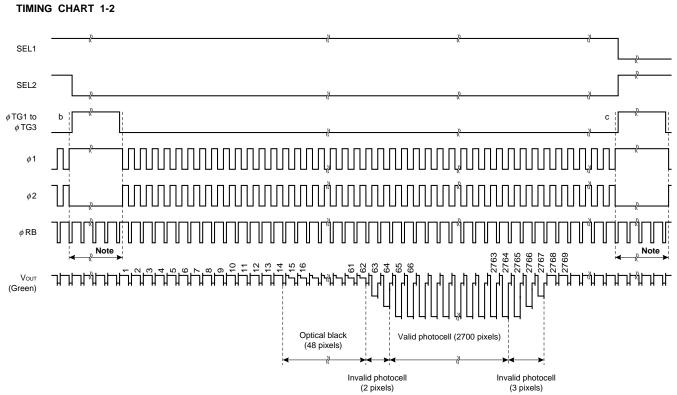
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#### **RGB SELECT FUNCTION**

RGB sel	ect input	Output color
SEL1	SEL2	Output color
High level	High level	Blue
High level	Low level	Green
Low level	High level	Red
Low level	Low level	Prohibited

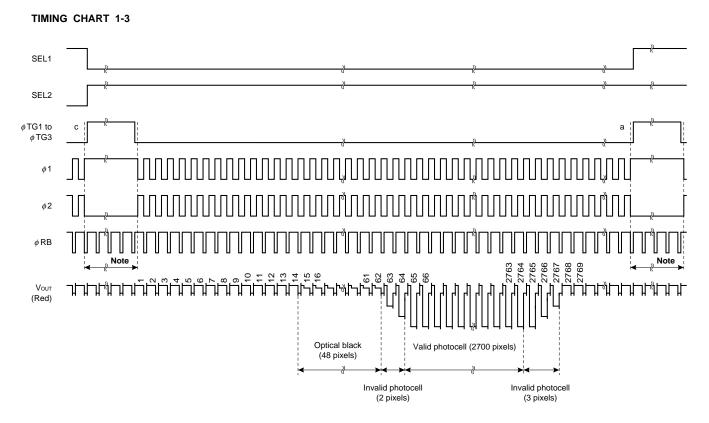


**Note** Input the  $\phi$ RB pluse continuously during this period, too.



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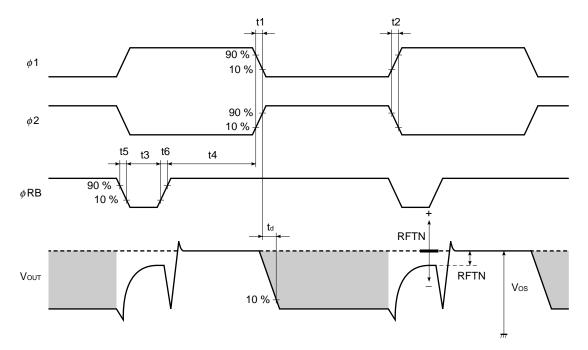
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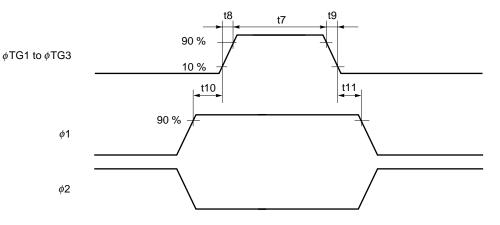
#### **Note** Input the $\phi$ RB pluse continuously during this period, too.

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#### TIMING CHART 2 (for each color)

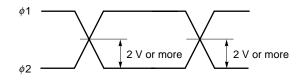


#### $\phi$ TG1 to $\phi$ TG3, $\phi$ 1, $\phi$ 2 TIMING CHART



Symbol	MIN.	TYP.	MAX.	Unit
t1, t2	0	25		ns
t3	30	50		ns
t4	150	250		ns
t5, t6	0	25		ns
t7	3000	10000		ns
t8, t9	0	50		ns
t10, t11	900	1000		ns

#### $\phi$ 1, $\phi$ 2 cross points

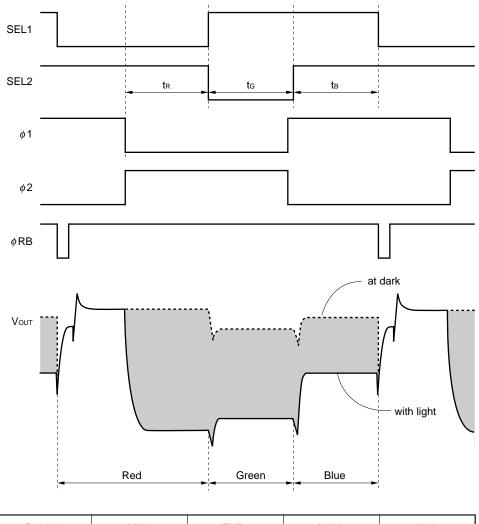




**Remark** Adjust cross points of  $\phi$ 1 and  $\phi$ 2 with input resistance of each pin. **10** 

#### **APPLICATION TIMING EXAMPLE (for reference)**

The  $\mu$ PD3794 can be operated under the following timing to switch Red, Green, and Blue outputs and get each color data in a 1-pixel period. However the offset level of each color is not the same. Therefore, offset level compensation is required to each color by using each color's data at dark or the optical black pixels. The following timing and parameters are for reference only.



Symbol	MIN.	TYP.	MAX.	Unit
tr, tg, tв	300	—		ns

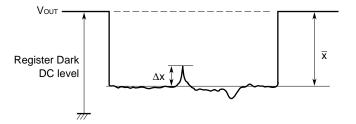
#### DEFINITIONS OF CHARACTERISTIC ITEMS

- Saturation voltage: V<sub>sat</sub>
   Output signal voltage at which the response linearity is lost.
- 2. Saturation exposure: SE Product of intensity of illumination (Ix) and storage time (s) when saturation of output voltage occurs.
- 3. Photo response non-uniformity: PRNU

The output signal non-uniformity of all the valid pixels when the photosensitive surface is applied with the light of uniform illumination. This is calculated by the following formula.

PRNU (%) = 
$$\frac{\Delta x}{\overline{x}} \times 100$$
  
 $\Delta x : \text{maximum of } |x_j - \overline{x}|$   
 $\overline{x} = \frac{\sum_{j=1}^{2700} x_j}{2700}$ 

x<sub>j</sub>: Output voltage of valid pixel number j



4. Average dark signal: ADS

Average output signal voltage of all the valid pixels at light shielding. This is calculated by the following formula.

ADS (mV) = 
$$\frac{\sum_{j=1}^{2700} d_j}{2700}$$

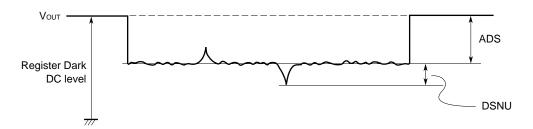
dj : Dark signal of valid pixel number j

5. Dark signal non-uniformity: DSNU

Absolute maximum of the difference between ADS and voltage of the highest or lowest output pixel of all the valid pixels at light shielding. This is calculated by the following formula.

DSNU (mV) : maximum of  $|d_j - ADS|_{j=1 \text{ to } 2700}$ 

dj : Dark signal of valid pixel number j



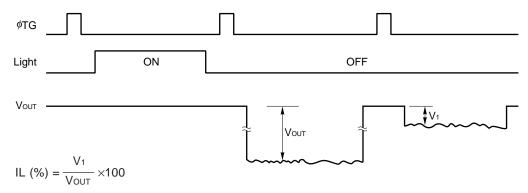
- Output impedance: Zo
   Impedance of the output pins viewed from outside.
- 7. Response: R

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Output voltage divided by exposure (Ix•s). Note that the response varies with a light source (spectral characteristic).

8. Image Lag: IL

The rate between the last output voltage and the next one after read out the data of a line.

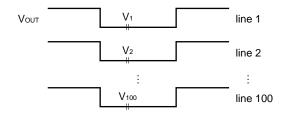


9. Random noise:  $\sigma$ 

Random noise  $\sigma$  is defined as the standard deviation of a valid pixel output signal with 100 times (=100 lines) data sampling at dark (light shielding).

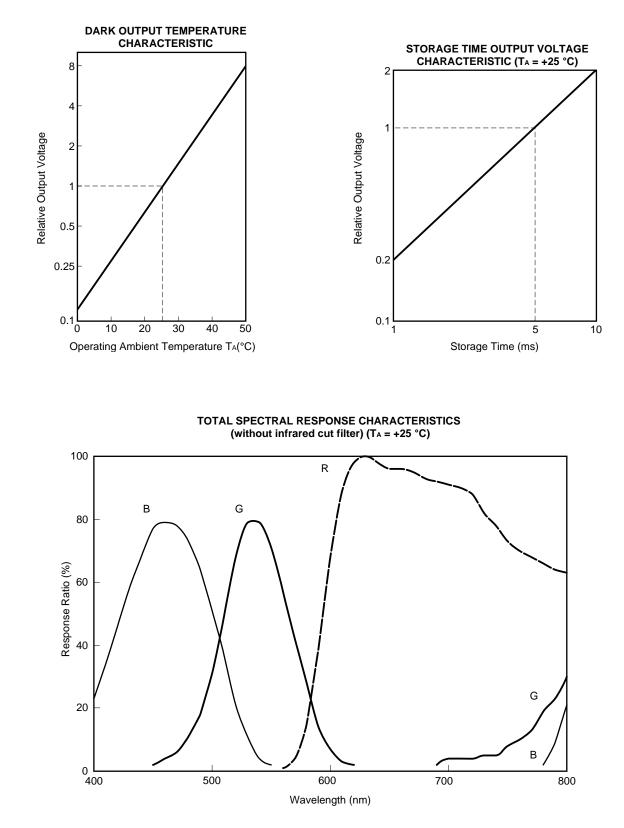
$$\sigma (mV) = \sqrt{\frac{\sum_{i=1}^{100} (V_i - \overline{V})^2}{100}} \quad , \ \overline{V} = \frac{1}{100} \sum_{i=1}^{100} V_i$$

Vi: A valid pixel output signal among all of the valid pixels for each color

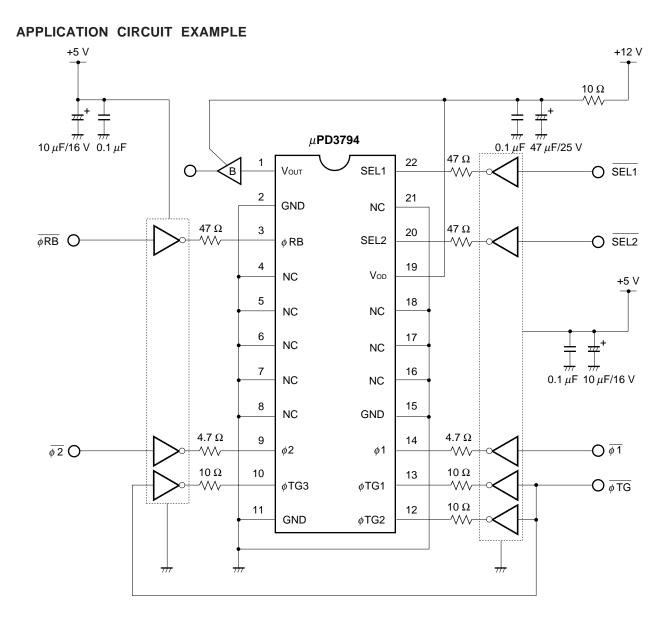


This is measured by the DC level sampling of only the signal level, not by CDS (Correlated Double Sampling).

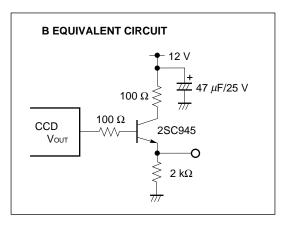
#### STANDARD CHARACTERISTIC CURVES



14



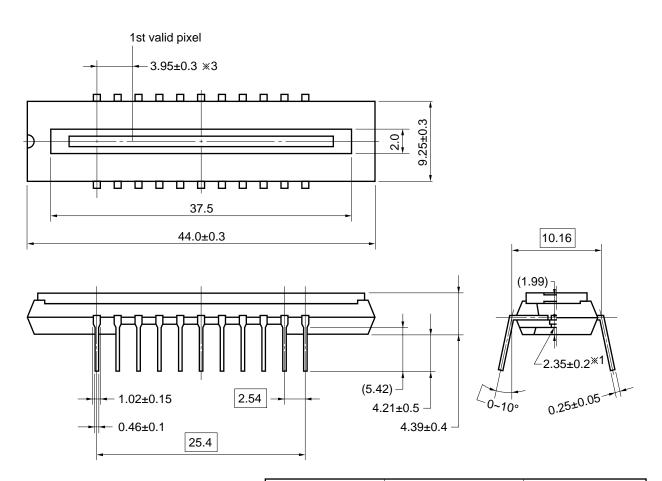




#### PACKAGE DRAWING

# CCD LINEAR IMAGE SENSOR 22PIN PLASTIC DIP (400 mil)

(Unit : mm)



Name	Dimensions	Refractive index
Plastic cap	42.9 x 8.35 x 0.7 <sup>×2</sup>	1.5

 $\times 1$  The bottom of the package --- The surface of the chip

- \*2 The thickness of the cap over the chip
- \*3 The 1st valid pixel  $\rightarrow$  The center of the pin 1.

22C-1CCD-PKG10-1

#### **RECOMMENDED SOLDERING CONDITIONS**

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

For more details, refer to our document "Semiconductor Device Mounting Technology Manual"(C10535E).

#### Type of Through-hole Device

#### µPD3794CY: CCD linear image sensor 22-pin plastic DIP (400 mil)

Process	Conditions
Partial heating method	Pin temperature: 260 °C or below, Heat Time: 10 seconds or less (per pin)

Caution During assembly care should be taken to prevent solder or flux from contacting the plastic cap. The optical characteristics could be degraded by such contact.

# -NOTES ON CLEANING THE PLASTIC CAP-

# **(1)** CLEANING THE PLASTIC CAP

Care should be taken when cleaning the surface to prevent scratches. The optical characteristics of the CCD will be degraded if the cap is scratched during cleaning.

We recommend cleaning the cap with a soft cloth moistened with one of the recommended solvents below. Excessive pressure should not be applied to the cap during cleaning. If the cap requires multiple cleanings it is recommended that a clean surface or cloth be used.

# **(2)** RECOMMENDED SOLVENTS

The following are the recommended solvents for cleaning the CCD plastic cap. Use of solvents other than these could result in optical or physical degradation in the plastic cap. Please consult your sales office when considering an alternative solvent.

Solvents	Symbol
Ethyl Alcohol	EtOH
Methyl Alcohol	MeOH
Isopropyl Alcohol	IPA
N-methyl Pyrrolidone	NMP

# -NOTES FOR CMOS DEVICES -

# **①** PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

# **(2)** HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

# **③** STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function. [MEMO]

The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

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While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

- Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.

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